



Industrial Grade Low-Skew, 1-to-2 LVCMOS/LVTTL Fanout Buffer

Features

- → Two LVCMOS/LVTTL Outputs
- → LVCMOS/LVTTL Clock Input Accepts LVCMOS or LVTTL Input Levels
- → Maximum Output Frequency: 250MHz
- → Output Skew: 25ps (Typical)
- → Full 3.3V, 2.5V Operation Modes
- → Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- → Halogen and Antimony Free "Green" Device (Note 3)
- → For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

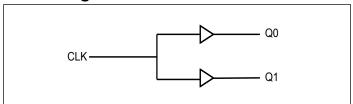
https://www.diodes.com/quality/product-definitions/

- → Packaging (Pb-free & Green):
 - Small 8-pin SOIC (W) package saves board space

Description

The PI6C49CB02J is an industrial grade low-skew, 1-to-2 LVCMOS/LVTTL high-performance fanout buffer. The PI6C49CB02J has a single-ended clock input. The single-ended clock input accepts LVCMOS or LVTTL input levels. The PI6C49CB02J features a pair of LVCMOS/LVTTL outputs. Guaranteed output and part-to-part skew characteristics make the PI6C49CB02J ideal for clock distribution applications demanding well-defined performance and repeatability.

Block Diagram



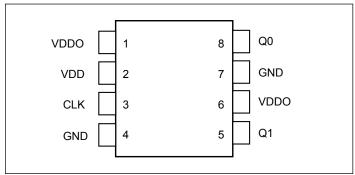
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





Pin Configuration



Pin Descriptions

Pin#	Pin Name	Pin Type		Pin Description
1, 6	VDDO	Power	_	Output Supply Pins
2	VDD	Power	_	Core Supply Pin
3	CLK	Input	Pull-down	LVCMOS/LVTTL Clock Input
4, 7	GND	Power	_	Power Supply Ground
5	Q1	Output	_	Single Clock Output. LVCMOS/LVTTL Interface Levels.
8	Q0	Output	_	Single Clock Output. LVCMOS/LVTTL Interface Levels.

Note: Pulldown refer to internal input resistors, typical values in Pin Characteristics table.

Pin Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
C_{N}	Capacitance	_	_	4	_	pF
R _{PULLDOWN}	Input Pull-down Resistor	_	_	51	_	kΩ
ROUT	Output Impedance	_	5	7	12	Ω





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Maximum Supply Voltage, VDD, VDDO	4.6V
Inputs, V ₁	0.5V to VDD+0.5V
Output, \dot{V}_{0}	
Storage Temperature	
ESD Protection (HBM)	2000V
Junction Temperature	125°C (Max)

Note:

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the DC Characteristics or AC Characteristics is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Recommended Operation Conditions

Parameter	Min.	Тур.	Max.	Units
Ambient Operating Temperature	-40	_	+105	°C
Power Supply Voltage (measured in respect to GND)		_	+3.465	V

Power Supply DC Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
WDD	Core Supply Voltage	3.3V Operation	3.135	3.3	3.465	3.7
VDD		2.5V Operation	2.375	2.5	2.625	V
VDDO Output Power Supply Voltage	3.3V Supply	3.135	3.3	3.465	17	
	Output Power Supply Voltage	2.5V Supply	2.375	2.5	2.625	V
IDD	Power Supply Current	$T_A = -40$ °C to 85°C	_	_	5	mA
IDDO	Output Supply Current	Unloaded, 25 MHz, T _A = -40°C to 85°C	_	_	6.5	mA
IDD	Power Supply Current	$T_A = -40^{\circ}\text{C to } 105^{\circ}\text{C}$	_	_	5	mA
IDDO	Output Supply Current	Unloaded, 25 MHz, T _A = -40°C to 105°C	_	_	6.5	mA

Note: Parameters measured up to f_{max} unless otherwise noted.





LVCMOS / LVTTL DC Characteristics, $T_A = -40^{\circ} C$ to $105^{\circ} C$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
3.7	T TT: 1 X7 1.	VDD = 3.3V	2	_	VDD+0.3	V	
$V_{_{\mathrm{IH}}}$	Input High Voltage	VDD = 2.5V	1.7	_	VDD+0.3		
3.7	Innet I am Wilton	VDD = 3.3V	-0.3	_	0.8	17	
V_{IL}	Input Low Voltage	VDD = 2.5V	-0.3	_	0.8	V	
т	Lange III of Comment	$VDD = V_{IN} = 3.465V$	_	_	100	4	
I _{IH} Input High Current	Input High Current	$VDD = V_{IN} = 2.625V$	_	_	80	μΑ	
T T	Immut I over Commont	$VDD = 3.465V, V_{IN} = 0V$	-5	_	_	1	
1 _{IL}	Input Low Current	$VDD = 2.625V, V_{IN} = 0V$	-5	_	_	μΑ	
77	Outmut High Waltage	$ VDDO = 3.3V I_{OH} = -100\mu A$	2.9	_	_	V	
V _{OH}	Output High Voltage	$ VDDO = 2.5V I_{OH} = -100\mu A$	2.2	_	_	V	
V _{OL}	Output Low Voltage	$VDDO = 3.3V \mid I_{OL} = 100 \mu A$	_	_	0.2	V	
	Output Low Voltage	$ VDDO = 2.5V I_{OL} = 100\mu A$	_	_	0.2	V	

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AC Characteristics, VDD = $3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $105^{\circ}C$

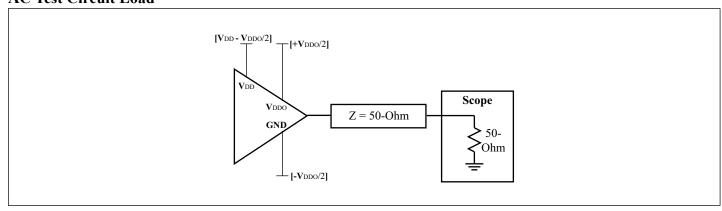
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
C	0	VDDO = 3.3V	4	_	250	MHz
f_{MAX}	Output Frequency	VDDO = 2.5V	4	_	250	
	D D 1 I III 1(1)	VDDO = 3.3V, f ≤ 250MHz	1.4	_	2.2	
tp _{LH}	Propagation Delay, Low-to-High ⁽¹⁾	$VDDO = 2.5V, f \le 250MHz$	1.5	_	3.0	ns
tsk(o)	Output Skew ⁽²⁾	_	_	25	80	ps
tsk(pp)	Part-to-Part Skew ⁽³⁾	_	_	250	800	ps
	Output Rise Time ⁽⁴⁾	VDDO = 3.3V	100	300	400	ps
$t_{\scriptscriptstyle \mathrm{R}}$		VDDO = 2.5V	100	350	500	
t _F Output Fall Time ⁽⁴⁾	Oct. 11 T: (4)	VDDO = 3.3V	100	300	400	
	Output Fall Time(4)	VDDO = 2.5V	100	350	500	ps
		<i>f</i> ≤133MHz	48	_	52	%
odc	Output Duty Cycle(5)	$133 \text{MHz} < f \le 200 \text{MHz}$	47	_	53	%
		$200 \text{MHz} < f \le 250 \text{MHz}$	47	_	53	%
t _{jit}	Additive RMS Jitter	156.25MHz (@12kHz to 20MHz)	_	0.1	_	ps
	,	125MHz (@12kHz to 20MHz)	_	0.07	_	ps

Note:

Parameters measured at f $_{\rm MAX}$ unless otherwise noted.

- 1. Measured from VDD/2 of the input to VDDO/2 of the output.
- 2. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at VDDO/2.
- 3. Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at VDDO/2.
- 4. Defined from 20% to 80%.
- 5. Measured at VDDO/2.

AC Test Circuit Load







AC Characteristics, $VDD = 2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $105^{\circ}C$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
f_{MAX}	Output Frequency	VDDO = 2.5V	4	_	250	MHz
tp _{LH}	Propagation Delay, Low-to-High ⁽¹⁾	$VDDO = 2.5V, f \le 250MHz$	1.5	_	2.8	ns
tsk(o)	Output Skew ⁽²⁾	_	_	25	75	ps
tsk(pp)	Part-to-Part Skew ⁽³⁾	_	_	250	800	ps
$t_{_{ m R}}$	Output Rise Time ⁽⁴⁾	VDDO = 2.5V	100	350	500	ps
$\mathbf{t}_{_{\mathrm{F}}}$	Output Fall Time ⁽⁴⁾	VDDO = 2.5V	100	350	500	ps
		<i>f</i> ≤ 133MHz	48	_	52	%
odc	Output Duty Cycle ⁽⁵⁾	$133 \text{MHz} < f \le 200 \text{MHz}$	47	_	53	%
		$200 \text{MHz} < f \le 250 \text{MHz}$	42	_	58	%
t _{jit}	A 1 ltc DMC ltu	156.25MHz (@12kHz to 20MHz)	_	0.1	_	ps
	Additive RMS Jitter	125MHz (@12kHz to 20MHz)	_	0.07	_	ps

Note:

Parameters measured at f $_{\mbox{\tiny MAX}}$ unless otherwise noted.

- 1. Measured from VDD/2 of the input to VDDO/2 of the output.
- 2. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at VDDO/2.
- 3. Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at VDDO/2.
- 4. Defined from 20% to 80%.
- 5. Measured at VDDO/2.

Part Marking

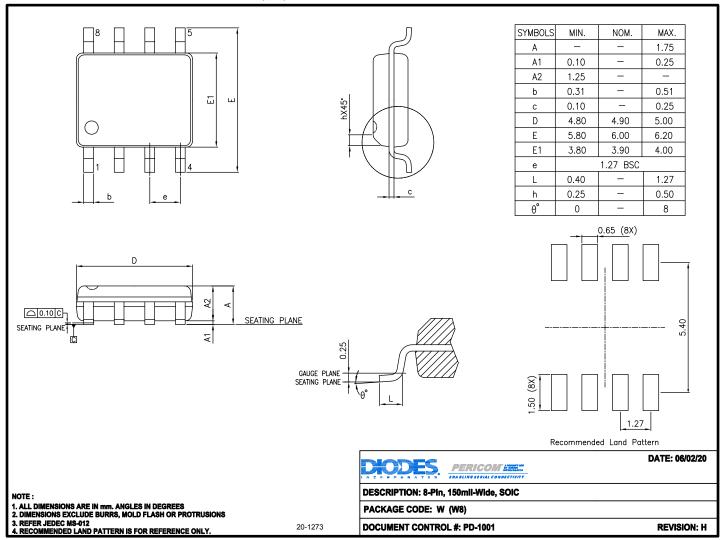


YY: Year WW: Workweek 1st X: Assembly Code 2nd X: Fab Code





Packaging Mechanical: 8-SOIC (W)



For latest package information:

See http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/.

Ordering Information

Ordering Code	Package Code	Package Description
PI6C49CB02JWEX	W	8-pin, 150mil-Wide (SOIC)

Notes:

- $1.\ No\ purposely\ added\ lead.\ Fully\ EU\ Directive\ 2002/95/EC\ (RoHS),\ 2011/65/EU\ (RoHS\ 2)\ \&\ 2015/863/EU\ (RoHS\ 3)\ compliant.$
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
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- 4. J = Industrial Grade
- 5. E = Pb-free and Green
- 6. X suffix = Tape/Reel





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